

# MOSPEC

## COMPLEMENTARY SILICON POWER TRANSISTORS

The MJ15003 and MJ15004 are power base power transistors designed for high power audio, disk head positioners, linear amplifiers, switching regulators, and other linear applications.

### FEATURES:

- \* High Power Dissipation  
 $P_D = 250 \text{ W}$  ( $T_C = 25^\circ\text{C}$ )
- \* High DC Current Gain and Low Saturation Voltage  
 $hFE = 25(\text{Min}) @ I_C = 5.0 \text{ A}, V_{CE} = 2.0 \text{ V}$
- \* For Low Distortion Complementary Designs

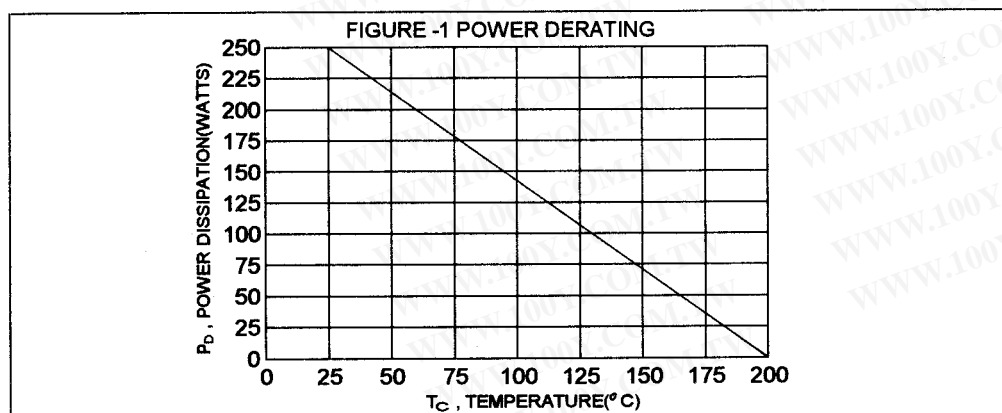
### MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CE(SUS)}$	140	V
Collector-Base Voltage	$V_{CBO}$	140	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Collector Current-Continuous Peak (1)	$I_C$ $I_{CM}$	20 30	A
Base Current-Continuous Peak (1)	$I_B$ $I_{BM}$	5.0 10	A
Total Power Dissipation @ $T_C=25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	250 1.43	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{STG}$	-65 to +200	$^\circ\text{C}$

(1) Pulse Test: Pulse width = 5 ms, Duty Cycle < 10%

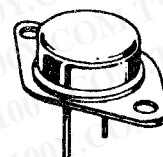
### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	0.70	$^\circ\text{C/W}$

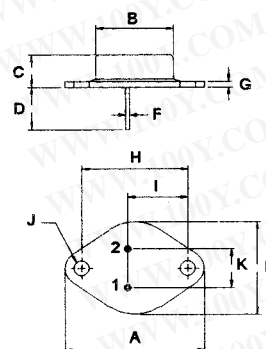


NPN PNP  
 MJ15003 MJ15004

20 AMPERE  
 COMPLEMENTARY SILICON  
 POWER TRANSISTORS  
 140 VOLTS  
 250 WATTS



TO-3



PIN 1. BASE  
 2. EMITTER  
 COLLECTOR (CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

**ELECTRICAL CHARACTERISTICS (  $T_C = 25^\circ\text{C}$  unless otherwise noted )**

Characteristic	Sym./Unit	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector - Emitter Sustaining Voltage (2) ( $I_C = 200\text{ mA}$ , $I_B = 0$ )	$V_{CEO(sus)}$	140		V
Collector Cutoff Current ( $V_{CE} = 140\text{ V}$ , $I_B = 0$ )	$I_{CO}$		250	$\mu\text{A}$
Collector Cutoff Current ( $V_{CE} = 140\text{ V}$ , $V_{BE(off)} = 1.5\text{ V}$ ) ( $V_{CE} = 140\text{ V}$ , $V_{BE(off)} = 1.5\text{ V}$ , $T_C = 150^\circ\text{C}$ )	$I_{CEX}$		100 2.0	$\mu\text{A}$ mA
Emitter Cutoff Current ( $V_{EB} = 5.0\text{ V}$ , $I_C = 0$ )	$I_{EBO}$		100	$\mu\text{A}$

**ON CHARACTERISTICS (2)**

DC Current Gain ( $I_C = 5.0\text{ A}$ , $V_{CE} = 2.0\text{ V}$ )	hFE	25	150	
Collector - Emitter Saturation Voltage ( $I_C = 5.0\text{ A}$ , $I_B = 500\text{ mA}$ )	$V_{CE(sat)}$		1.0	V
Base - Emitter On Voltage ( $I_C = 5.0\text{ A}$ , $V_{CE} = 2.0\text{ V}$ )	$V_{BE(on)}$		2.0	V

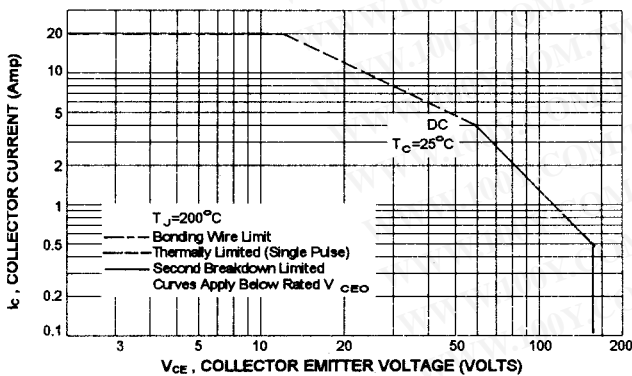
**DYNAMIC CHARACTERISTICS**

Current Gain - Bandwidth Product (3) ( $I_C = 500\text{ mA}$ , $V_{CE} = 10\text{ V}$ , $f = 0.5\text{ MHz}$ )	$f_T$	2.0		MHz
Output capacitance ( $V_{CB} = 4.0\text{ V}$ , $I_E = 0$ , $f = 1\text{ MHz}$ )	$C_{ob}$		1000	pF

(2) Pulse Test: Pulse width =  $300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

(3)  $f_T = |h_{fe}| \cdot f_{test}$

FIG-2 FORWARD BIAS SAFE OPERATING AREA



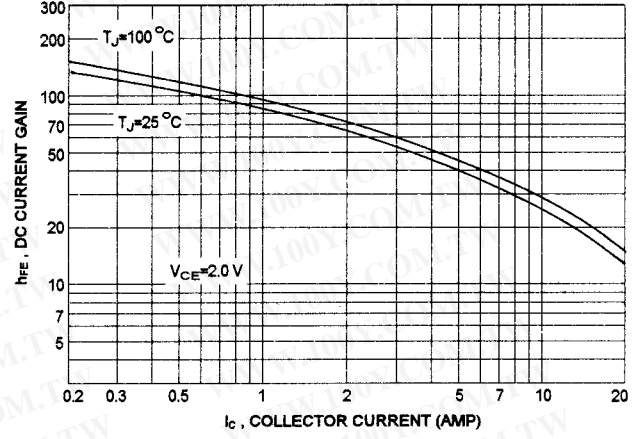
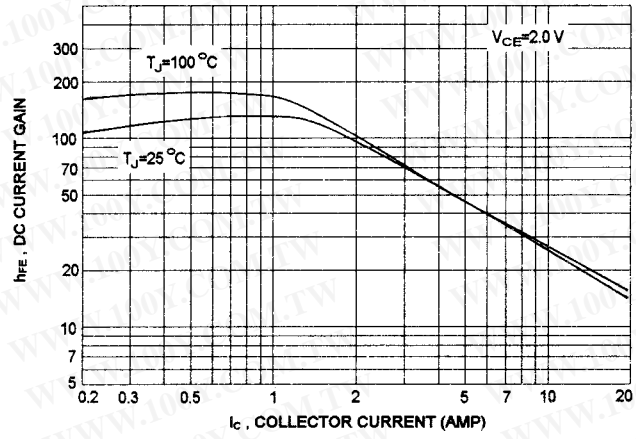
There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of FIG-2 is base on  $T_{J(PK)} = 200^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

MJ15003

DC CURRENT GAIN

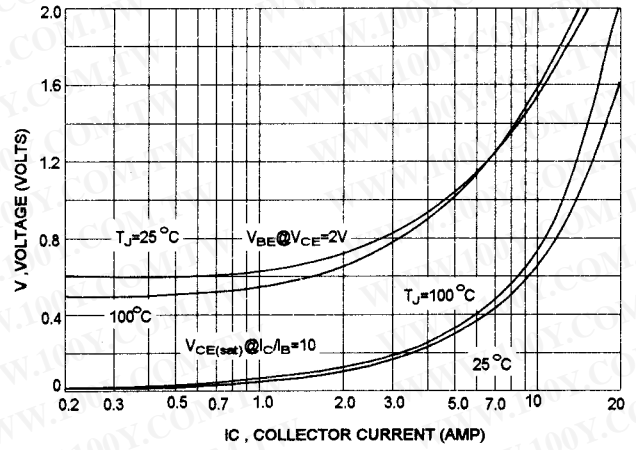
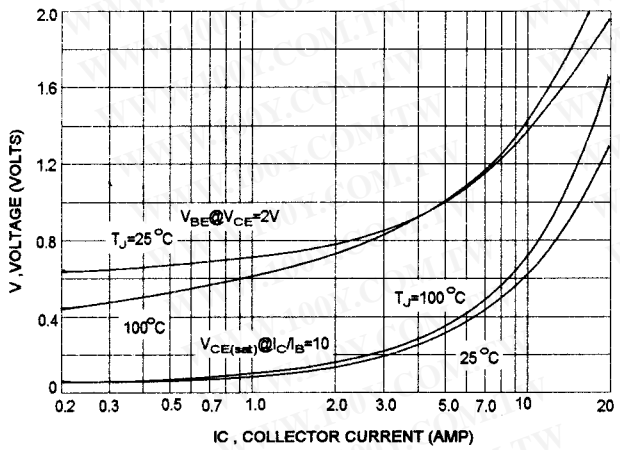
MJ15004



"ON" VOLTAGE

MJ15003

MJ15004



CAPACITANCES

CURRENT GAIN- BANDWIDTH PRODUCT

